# PUB4120 (PU4120), PUB4420 (PU4420)

### Silicon NPN triple diffusion planar type darlington

#### For power amplification

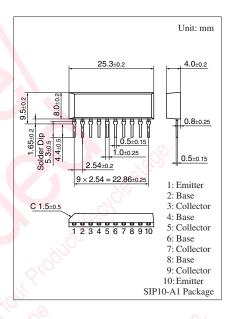
Complementary to PUB4220 (PU4220), PUB4520 (PU4520)

#### Features

- $\bullet$  High forward current transfer ratio  $h_{FE}$
- High-speed switching
- PUB4120 (PU4120): NPN 4 elements PUB4420 (PU4420): NPN 2 elements × 2

#### Absolute Maximum Ratings $T_C = 25^{\circ}C$

Parameter	Symbol	Rating	Unit	
Collector-base voltage (Emitter open)	V <sub>CBO</sub>	60	V	
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	60	V	
Emitter-base voltage (Collector open)	V <sub>EBO</sub>	5	V	
Collector current	I <sub>C</sub>	4	A	
Peak collector current	I <sub>CP</sub>	8	А	
Collector power dissipation	P <sub>C</sub>	15	W	
$T_a = 25^{\circ}C$		3.5		
Junction temperature	Tj	150	°C	
Storage temperature	T <sub>stg</sub>	-55 to +150	°C	



#### Electrical Characteristics $T_{C} = 25^{\circ}C \pm 3^{\circ}C$

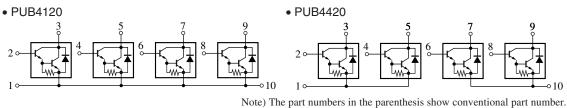
Symbol	Conditions	Min	Тур	Max	Unit
V <sub>CEO</sub>	$I_{\rm C} = 30 \text{ mA}, I_{\rm B} = 0$	60		1. 16	v
V <sub>BE</sub>	$V_{CE} = 3 V, I_C = 3 A$	0	XO	2.5	V
I <sub>CBO</sub>	$V_{CB} = 60 \text{ V}, I_E = 0$	3.1	0	200	μΑ
I <sub>CEO</sub>	$V_{CE} = 30 \text{ V}, I_B = 0$	02		500	μΑ
I <sub>EBO</sub>	$V_{EB} = 5 V, I_C = 0$	\$2°	S	2	mA
h <sub>FE1</sub>	$V_{CE} = 3 V, I_C = 0.5 A$	1 000			
h <sub>FE2</sub> *	$V_{CE} = 3 V, I_C = 3 A$	1 000		10000	
V <sub>CE(sat)</sub>	$I_{\rm C} = 3 \text{ A}, I_{\rm B} = 12 \text{ mA}$			2.0	V
f <sub>T</sub>	$V_{CE} = 10 \text{ V}, I_C = 0.5 \text{ A}, f = 1 \text{ MHz}$		20		MHz
t <sub>on</sub>	$I_C = 3 A$		0.5		μs
t <sub>stg</sub>	$I_{B1} = 12 \text{ mA}, I_{B2} = -12 \text{ mA}$		4.0		μs
t <sub>f</sub>	$V_{CC} = 50 \text{ V}$		1.0		μs
	$\begin{tabular}{ c c c c } \hline Symbol \\ \hline V_{CEO} \\ \hline V_{BE} \\ \hline I_{CBO} \\ \hline I_{CEO} \\ \hline I_{EBO} \\ \hline h_{FE1} \\ \hline h_{FE2} \\ * \\ \hline V_{CE(sat)} \\ \hline f_T \\ \hline t_{on} \\ \hline t_{stg} \end{tabular}$	$\begin{array}{c c c c c c c c c c c c c c c c c c c $	$\begin{array}{c c c c c c c c c c c c c c c c c c c $	$\begin{array}{c c c c c c c c c c c c c c c c c c c $	$\begin{array}{c c c c c c c c c c c c c c c c c c c $

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

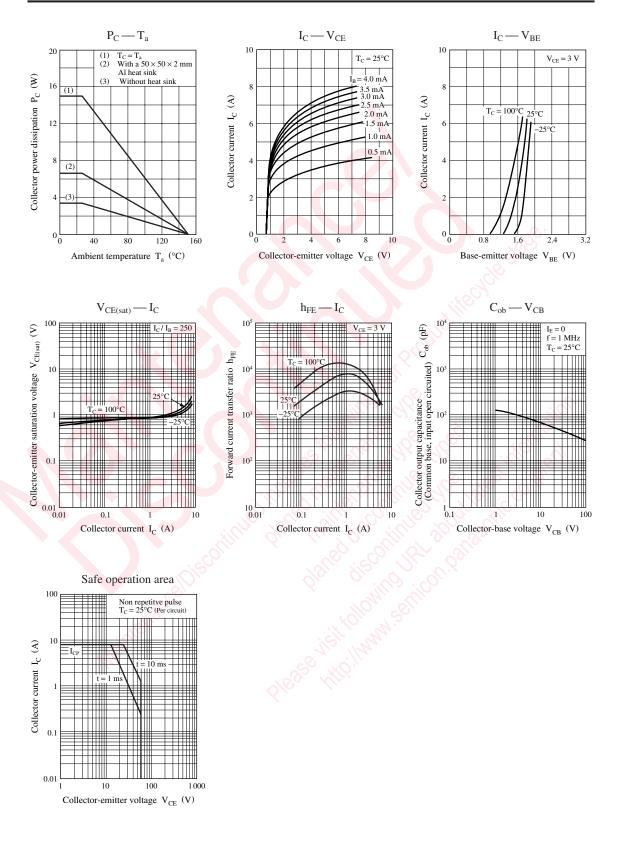
2. \*: Rank classification

Rank	Free	Р	Q	
$h_{\rm FE}$	1000 to 10000	2000 to 10000	1000 to 5000	

#### Internal Connection



### Panasonic



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